EH2900TTS-37.056M



Series — RoHS Compliant (Pb-free) 1.8V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Oscillator <u>T TS -37.056M</u>

Nominal Frequency 37.056MHz

Pin 1 Connection

Tri-State (High Impedance) - Duty Cycle 50 ±5(%)

EH29 00

ture Range _____ 5

E 1	E07		AL 0	DEO		
EL	EC I	RIC	AL S	PEC	JIFIO	ONS

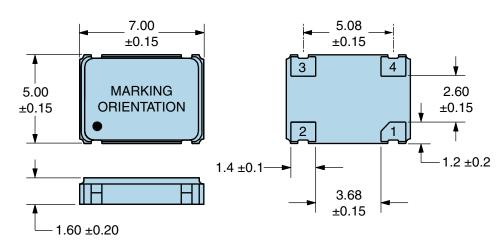
Aging at 25°CSupply Voltage Change, Output Load Change, First Year Aging at 25°, 260°C Reflow, Shock, and Vibration)Aging at 25°C±5ppm/Year MaximumOperating Temperature Range0°C to +70°CSupply Voltage1.8Vdc ±5%Input Current4mA Maximum (No Load)Output Voltage Logic High (Voh)90% of Vdd Minimum (IOH = -8mA)Output Voltage Logic Low (Vol)10% of Vdd Maximum (IOL = +8mA)Rise/Fall Time6nSec Maximum (Measured at 20% to 80% of waveform)Duty Cycle50 ±5(%) (Measured at 50% of waveform)Load Drive Capability15pF MaximumOutput Logic TypeCMOSPin 1 ConnectionTri-State (High Impedance)Tri-State Input Voltage (Vih and Vil)90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)Standby Current10µA Maximum (Pin 1 = Ground)Absolute Clock Jitter±100pSec Maximum	Nominal Frequency	37.056MHz
Operating Temperature Range0°C to +70°CSupply Voltage1.8Vdc ±5%Input Current4mA Maximum (No Load)Output Voltage Logic High (Voh)90% of Vdd Minimum (IOH = -8mA)Output Voltage Logic Low (Vol)10% of Vdd Maximum (IOL = +8mA)Rise/Fall Time6nSec Maximum (Measured at 20% to 80% of waveform)Duty Cycle50 ±5(%) (Measured at 50% of waveform)Load Drive Capability15pF MaximumOutput Logic TypeCMOSPin 1 ConnectionTri-State (High Impedance)Tri-State Input Voltage (Vih and Vil)90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)Standby Current10µA Maximum (Pin 1 = Ground)Absolute Clock Jitter±100pSec MaximumStart Up Time10mSec Maximum	Frequency Tolerance/Stability	Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°,
Supply Voltage1.8Vdc ±5%Input Current4mA Maximum (No Load)Output Voltage Logic High (Voh)90% of Vdd Minimum (IOH = -8mA)Output Voltage Logic Low (Vol)10% of Vdd Maximum (IOL = +8mA)Rise/Fall Time6nSec Maximum (Measured at 20% to 80% of waveform)Duty Cycle50 ±5(%) (Measured at 50% of waveform)Load Drive Capability15pF MaximumOutput Logic TypeCMOSPin 1 ConnectionTri-State (High Impedance)Tri-State Input Voltage (Vih and Vil)90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)Standby Current10µA Maximum (Pin 1 = Ground)Absolute Clock Jitter±100pSec Maximum	Aging at 25°C	±5ppm/Year Maximum
Input Current4mA Maximum (No Load)Output Voltage Logic High (Voh)90% of Vdd Minimum (IOH = -8mA)Output Voltage Logic Low (Vol)10% of Vdd Maximum (IOL = +8mA)Rise/Fall Time6nSec Maximum (Measured at 20% to 80% of waveform)Duty Cycle50 ±5(%) (Measured at 50% of waveform)Load Drive Capability15pF MaximumOutput Logic TypeCMOSPin 1 ConnectionTri-State (High Impedance)Tri-State Input Voltage (Vih and Vil)90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)Standby Current10µA Maximum (Pin 1 = Ground)Absolute Clock Jitter±100pSec MaximumStart Up Time10mSec Maximum	Operating Temperature Range	0°C to +70°C
Output Voltage Logic High (Voh)90% of Vdd Minimum (IOH = -8mA)Output Voltage Logic Low (Vol)10% of Vdd Maximum (IOL = +8mA)Rise/Fall Time6nSec Maximum (Measured at 20% to 80% of waveform)Duty Cycle50 ±5(%) (Measured at 50% of waveform)Load Drive Capability15pF MaximumOutput Logic TypeCMOSPin 1 ConnectionTri-State (High Impedance)Tri-State Input Voltage (Vih and Vil)90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)Standby Current10µA Maximum (Pin 1 = Ground)Absolute Clock Jitter±100pSec Maximum	Supply Voltage	1.8Vdc ±5%
Output Voltage Logic Low (Vol)10% of Vdd Maximum (IOL = +8mA)Rise/Fall Time6nSec Maximum (Measured at 20% to 80% of waveform)Duty Cycle50 ±5(%) (Measured at 50% of waveform)Load Drive Capability15pF MaximumOutput Logic TypeCMOSPin 1 ConnectionTri-State (High Impedance)Tri-State Input Voltage (Vih and Vil)90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)Standby Current10µA Maximum (Pin 1 = Ground)Absolute Clock Jitter±100pSec MaximumStart Up Time10mSec Maximum	Input Current	4mA Maximum (No Load)
Rise/Fall Time6nSec Maximum (Measured at 20% to 80% of waveform)Duty Cycle50 ±5(%) (Measured at 50% of waveform)Load Drive Capability15pF MaximumOutput Logic TypeCMOSPin 1 ConnectionTri-State (High Impedance)Tri-State Input Voltage (Vih and Vil)90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)Standby Current10µA Maximum (Pin 1 = Ground)Absolute Clock Jitter±100pSec MaximumStart Up Time10mSec Maximum	Output Voltage Logic High (Voh)	90% of Vdd Minimum (IOH = -8mA)
Duty Cycle50 ±5(%) (Measured at 50% of waveform)Load Drive Capability15pF MaximumOutput Logic TypeCMOSPin 1 ConnectionTri-State (High Impedance)Tri-State Input Voltage (Vih and Vil)90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)Standby Current10µA Maximum (Pin 1 = Ground)Absolute Clock Jitter±100pSec MaximumStart Up Time10mSec Maximum	Output Voltage Logic Low (Vol)	10% of Vdd Maximum (IOL = +8mA)
Load Drive Capability15pF MaximumOutput Logic TypeCMOSPin 1 ConnectionTri-State (High Impedance)Tri-State Input Voltage (Vih and Vil)90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance)Standby Current10µA Maximum (Pin 1 = Ground)Absolute Clock Jitter±100pSec MaximumStart Up Time10mSec Maximum	Rise/Fall Time	6nSec Maximum (Measured at 20% to 80% of waveform)
Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) 90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (Pin 1 = Ground) Absolute Clock Jitter ±100pSec Maximum Start Up Time 10mSec Maximum	Duty Cycle	50 ±5(%) (Measured at 50% of waveform)
Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) 90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (Pin 1 = Ground) Absolute Clock Jitter ±100pSec Maximum Start Up Time 10mSec Maximum	Load Drive Capability	15pF Maximum
Tri-State Input Voltage (Vih and Vil) 90% of Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (Pin 1 = Ground) Absolute Clock Jitter ±100pSec Maximum Start Up Time 10mSec Maximum	Output Logic Type	CMOS
Impedance) Standby Current 10µA Maximum (Pin 1 = Ground) Absolute Clock Jitter ±100pSec Maximum Start Up Time 10mSec Maximum	Pin 1 Connection	Tri-State (High Impedance)
Absolute Clock Jitter ±100pSec Maximum Start Up Time 10mSec Maximum	Tri-State Input Voltage (Vih and Vil)	
Start Up Time 10mSec Maximum	Standby Current	10μA Maximum (Pin 1 = Ground)
	Absolute Clock Jitter	±100pSec Maximum
Storage Temperature Range -55°C to +125°C	Start Up Time	10mSec Maximum
	Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-883, Method 2002, Condition B
Moisture Resistance	MIL-STD-883, Method 1004
Moisture Sensitivity	J-STD-020, MSL 1
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

EH2900TTS-37.056M

MECHANICAL DIMENSIONS (all dimensions in millimeters)



\cap	ECL	.IP]	TEK ®
	CORF	PORA	

PIN	CONNECTION
1	Tri-State
2	Case Ground
3	Output
4	Supply Voltage
LINE	MARKING
LINE 1	MARKING ECLIPTEK

Suggested Solder Pad Layout

All Dimensions in Millimeters

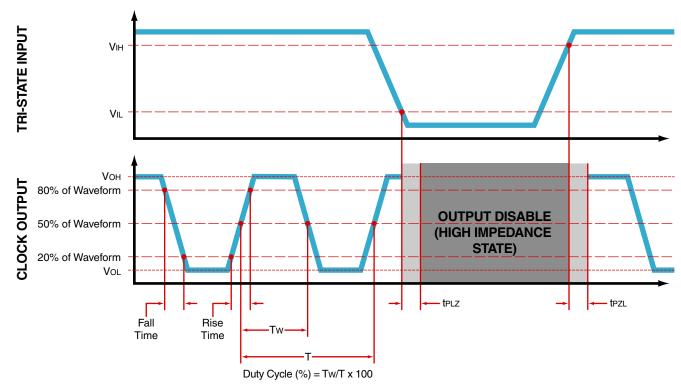


All Tolerances are ±0.1

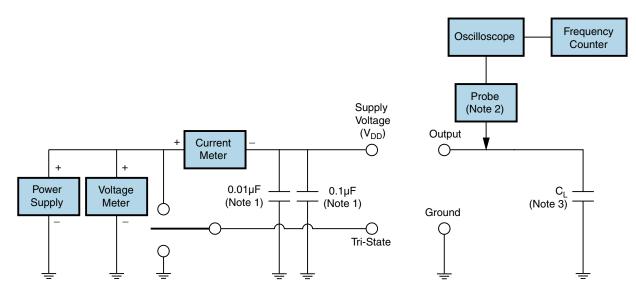
EH2900TTS-37.056M



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



- Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_{L} includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

EH2900TTS-37.056M

T_s MAX to T_L (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
 Temperature Maximum (T_s MAX) 	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t _p)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods

EH2900TTS-37.056M



Low Temperature Infrared/Convection 240°C

T_s MAX to T_L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
 Temperature Typical (T_s TYP) 	150°C
 Temperature Maximum (T_s MAX) 	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t _p)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)